



Product Overview

NTMS4801N: Power MOSFET 30V 12A 9 mOhm Single N-Channel SO-8

For complete documentation, see the data sheet

Product Description

This is a 30 V N-Channel Power MOSFET.

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- This is a PbFree Device

ApplicationsEnd Products

- DCDC Converters
 - Synchronous MOSFET
- Printers

Part Electrical Specifications

| Product | Compliance | Status | Channel Polarity | Configuration | $V_{DS}^{(BR)}$ Min (V) | $V_{GS}^{(max)}$ (V) | $V_{GS}^{(th)}$ Max (V) | I_D Max (A) | P_D Max (W) | $r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m) | $r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m) | $r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m) | Q_g Typ @ $V_{GS} = 4.5$ V (nC) | Q_g Typ @ $V_{GS} = 10$ V (nC) | Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC) | Q_{rr} Typ (nC) | C_{iss} Typ (pF) | C_{oss} Typ (pF) | C_{rss} Typ (pF) | Packaging Type |
|--------------|------------------------|--------|------------------|---------------|-------------------------|----------------------|-------------------------|---------------|---------------|---|---|--|-----------------------------------|----------------------------------|--------------------------------------|-------------------|--------------------|--------------------|--------------------|----------------|
| NTMS4801NR2G | Pb-free Halide free | Active | N-Channel | Single | 30 | 20 | 2.5 | 12 | 2.1 | | 12.5 | 9 | 12.2 | 25 | 4.4 | | 1630 | 288 | 150 | SOIC-8 |

For more information please contact your local sales support at www.onsemi.com

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